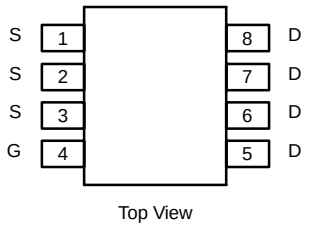
N-Channel 100-V (D-S) MOSFET

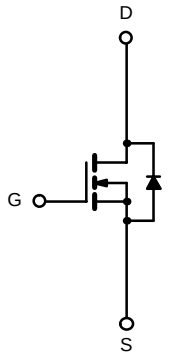
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.060 @ V_{GS} = 10 V	4.6
	0.080 @ V_{GS} = 6 V	4.0

TrenchFET® Power MOSFETs

SO-8



Top View



N-Channel MOSFET

Ordering Information: Si4482DY
Si4482DY-T1 (with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	4.6	A
	T_A = 70°C		3.7	
Pulsed Drain Current		I_{DM}	40	
Continuous Source Current (Diode Conduction)[a]		I_S	2.1	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.5	W
	T_A = 70°C		1.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Maximum Junction-to-Ambient[a]	R_{thJA}	50	°C/W

Notes
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

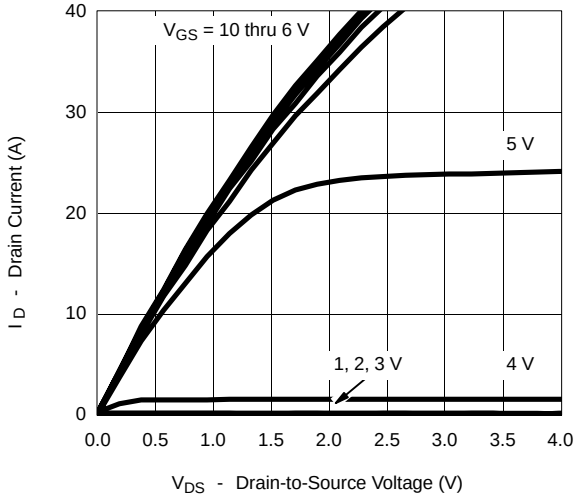
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	μA
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 55°C			20	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 4.6 A		0.045	0.060	Ω
		V_{GS} = 6 V, I_D = 4.0 A		0.050	0.080	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 4.6 A		20		S
Diode Forward Voltage[b]	V_{SD}	I_S = 2.1 A, V_{GS} = 0 V			1.2	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 4.6 A		30	50	nC
Gate-Source Charge	Q_{gs}			7.5		
Gate-Drain Charge	Q_{gd}			7		
Gate Resistance	R_g		1		4.4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 50 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		13	25	ns
Rise Time	t_r			12	25	
Turn-Off Delay Time	$t_{d(off)}$			60	90	
Fall Time	t_f			25	40	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 2.1 A, di/dt = 100 A/μs		50	80	

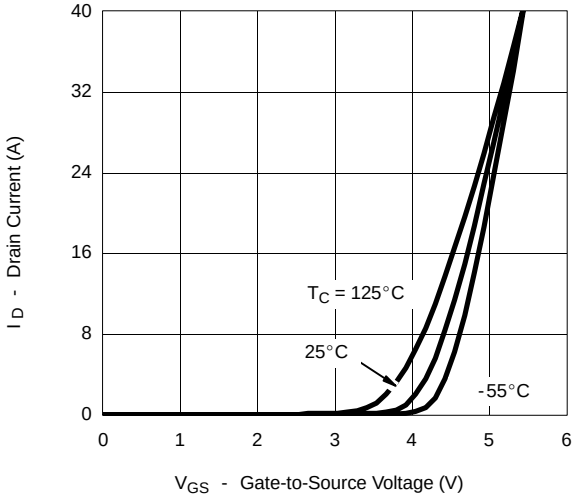
Notes
a. For design aid only; not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

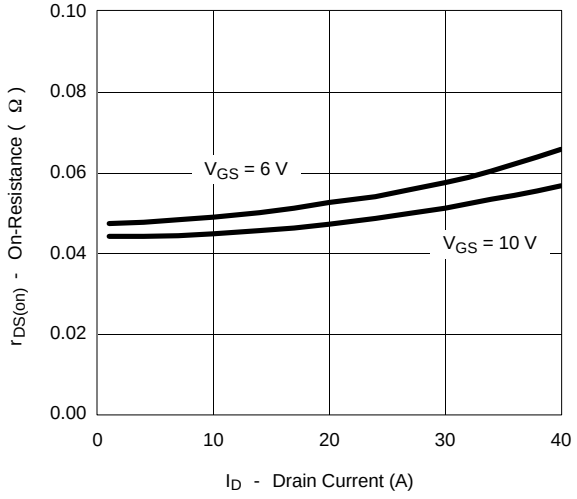
Output Characteristics



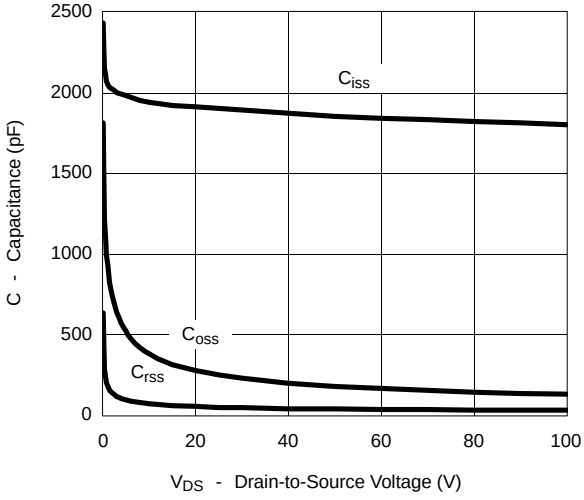
Transfer Characteristics



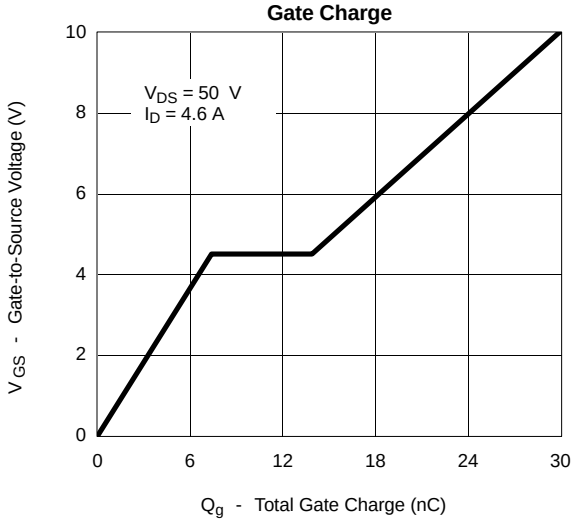
On-Resistance vs. Drain Current



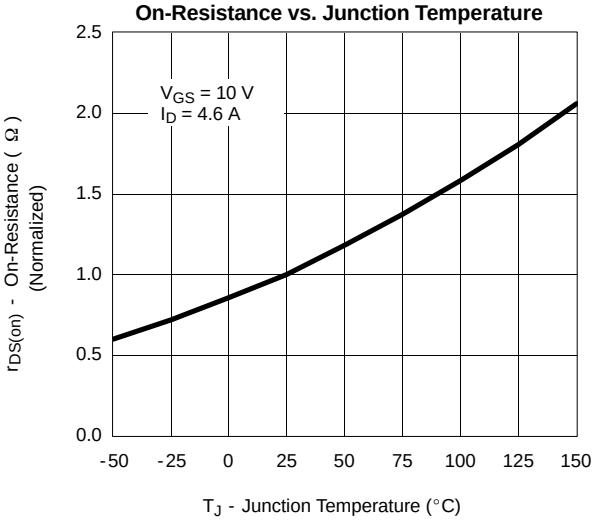
Capacitance



Gate Charge

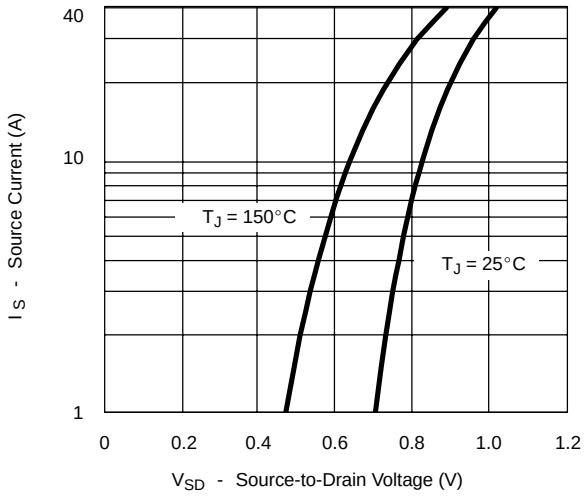


On-Resistance vs. Junction Temperature

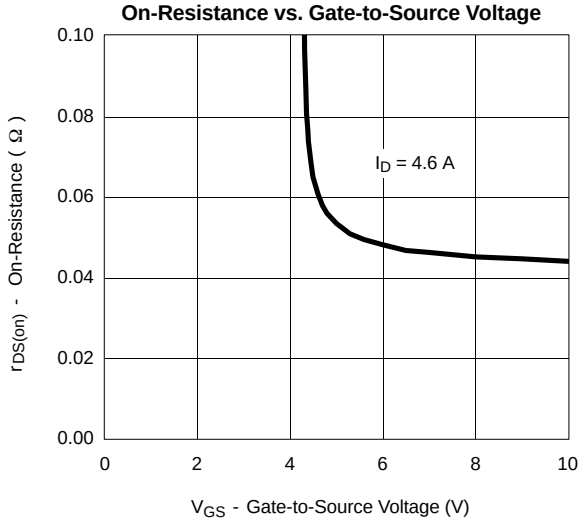


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

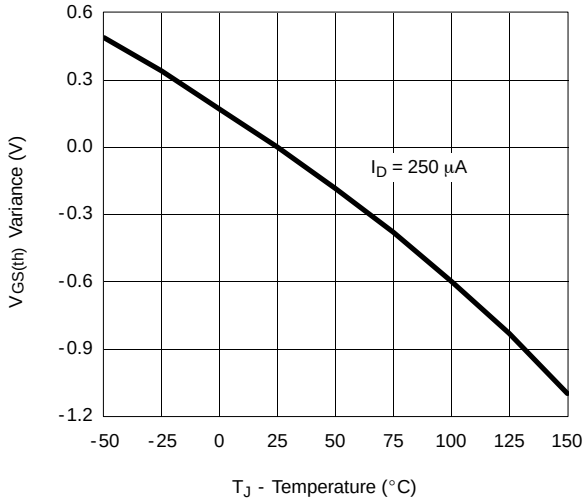
Source-Drain Diode Forward Voltage



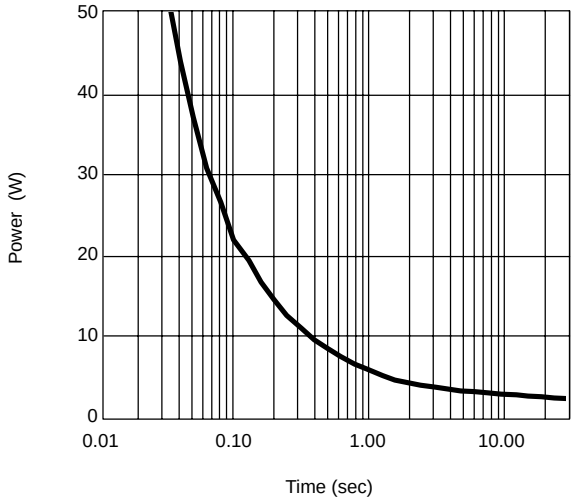
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient